To:

Facsimile Number: 703-872-9306

FEB 2 3 2005

From:

Texas Instruments Incorporated

Facsimile: 972-917-4418

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

**Applicant** 

Yuanning Chen, et al.

Docket Number: TI-35022.2

Serial No.: 10/719,279

Art Unit: 2813

Filed: 11/21/03

Examiner: Jack S.J. Chen

For:

Use of Hafnium Silicon Oxynitride as the Cap Layer of the

Sidewall Spacer

## CERTIFICATION OF FACSIMILE TRANSMISSION

I hereby certify that the following papers are being transmitted by facsimile to the U.S. Patent and Trademark Office on the date shown below:

Karen Vertz

## **FACSIMILE COVER SHEET**

X FACSIMILE COVER SHEET NEW APPLICATION DECLARATION ASSIGNMENT FORMAL DRAWINGS INFORMAL DRAWINGS CONTINUATION APP'N DIVISIONAL APP'N		AMENDMENT  X EOT 2 month  NOTICE OF APPEAL  APPEAL (# Pages)  ISSUE FEE & PUBLICATION FEE (1 Page)  REPLY BRIEF (IN TRIPLICATE) (# Pages)  ELECTION  X RCE
NAME OF INVENTOR(S): Yuanning Chen, et al.  TITLE OF INVENTION: Use of Hafnium Silicon Oxynitride as the Cap Layer of the Sidewall		Serial No.: 10/719,279 Filing Date: 11/21/03
TI FILE NO.:  TI – 35022.2  FAXED: 2-23-05  DUE: 1-18-05  ATTY/SECY: RAK/kiy	DEPOSIT ACCT. NO.: 20-0668	

This facstmile is intended only for the use of the address named and contains legally privileged and/or confidential information. If you are not the intended recipient of this telecopy, you are hereby notified that any dissemination, distribution, copying or use of this communication is strictly prohibited. Applicable privileges are not waived by virtue of the document having been transmitted by Facsimile. Any misdirected facsimiles should be returned to the sender by mail at the address indicated on this cover sheet.

Texas Instruments Incorporated PO Box 655474, MS 3999 Dallas, TX 75265-5474